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(54) **METHOD AND APPARATUS FOR PLACING TRANSISTORS IN PROXIMITY TO THROUGH-SILICON VIAS**

VERFAHREN UND VORRICHTUNG ZUR PLATZIERUNG VON TRANSISTOREN IN DER NÄHE VON THROUGH-SILICON VIAS

PROCÉDÉ ET APPAREIL POUR PLACER DES TRANSISTORS À PROXIMITÉ DE TROUS D'INTERCONNEXION TRAVERSANT LE SILICIUM (TSV)

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